

RKKY interaction in Mn-doped 4×4 Luttinger systems

Sonu Verma*, Arijit Kundu and Tarun Kanti Ghosh

Department of Physics, Indian Institute of Technology-Kanpur, Kanpur-208 016, India

*Author to whom correspondence should be addressed: sonuv@iitk.ac.in

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We consider Mn-doped bulk zinc-blende semiconductors described by the 4×4 Luttinger Hamiltonian. In these semiconductors, Mn atom acts as an acceptor providing the system a mobile hole, and also acts like a magnetic impurity of spin $S = 5/2$. We obtain exact analytical expressions of the hole mediated Ruderman-Kittel-Kasuya-Yoshida (RKKY) exchange interaction between two Mn^{2+} ions. The RKKY interaction of the Luttinger system consists of collinear Heisenberg-like and Ising-like interactions. The characteristic beating patterns appear in the range functions of the RKKY interaction owing to the presence of multiple Fermi wave-vectors of the underlying $j = 3/2$ states. As an application of the analytical form of the range function, from the finite temperature evaluation of the correlation functions, we calculate the contribution of RKKY interaction to the Curie-Weiss temperatures of a particular dilute magnetic semiconductor ZnMnTe where 4×4 Luttinger Hamiltonian is valid.

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I. INTRODUCTION

An electric control of the spin degree of freedom of a charge carrier is one of the primary objectives in spintronics and quantum information processing. The inherent spin-orbit interaction (SOI) arises due to the relativistic effect, which can be controlled by the spatial inversion symmetry breaking external electric field. The SOIs in materials give rise to many exotic phenomena. For example, the intrinsic spin Hall effect (SHE) arises solely due to the spin-orbit coupling even in absence of any magnetic impurities. After the theoretical proposal of intrinsic SHE¹ in p -doped III-V semiconductors described by the Luttinger Hamiltonian² for the spin-3/2 valence band, there is a resurgent research interest on various properties of the Luttinger Hamiltonian². This exotic phenomena has been realized experimentally in bulk n -doped semiconductors such as GaAs and InGaAs³ as well as in two-dimensional hole gas⁴. The hole gas is preferred over electron gas in the study of spin-related phenomena. This is because the p -orbital states of the hole wave function reduces the contact hyperfine interaction^{5,6}. This in turn enhances the spin coherence time of the hole charge carrier^{7,8}. A large number of theoretical studies e.g. spin Hall conductivity⁹, wave packet dynamics¹⁰⁻¹², Hartree-Fock analysis¹³, beating pattern in Friedel oscillations^{14,15}, magnetotransport coefficients¹⁶, electrical and optical conductivities¹⁷ of the Luttinger Hamiltonian have been carried out in recent past studies.

The mechanism of interaction between two localized magnetic impurities in spintronics materials attract considerable attention. The RKKY interaction¹⁸⁻²⁰ is an indirect exchange interaction between two magnetic impurities mediated by mobile charge carriers. This long-range spin-spin interaction plays a crucial role in magnetic ordering (ferromagnetic/antiferromagnetic) of the impurities and may help to understand the magnetic

properties of the host system. The nature of the mobile carriers (e.g. helicity, energy dispersion, spinor structure etc) determine the characteristics of the RKKY interaction. The role of the RKKY interaction in other condensed matter systems has also been studied extensively. For instance, magnetoresistance in multilayer structures²¹, topological states and Majorana fermions²². The Rashba spin-orbit coupling effect on RKKY interaction has been rigorously studied in 1D²³⁻²⁶, 2D²⁷⁻³² and 3D³³ electron systems. The strength of the range functions characterizing RKKY interaction in various systems oscillate with the distance between two magnetic impurities (R) and decays asymptotically as $1/R^\eta$ with η being the system dependent exponent. The oscillation frequency (in units of the distance R) is determined by the density and effective mass of the charge carriers and other material parameters.

The ferromagnetic ordering in Mn-doped zinc-blende semiconductors was first realized by Muneketa et al³⁴. Subsequently it has been established that Mn atom is the source of local magnetic moments and also provides mobile holes in many Mn-doped zinc-blende semiconductors (such as GaAs, GaP and ZnTe) and show up the Curie-Weiss temperatures from few kelvins to few hundred kelvins³⁵⁻⁴⁵.

There have been extensive theoretical studies of ferromagnetism in Mn-doped zinc blende semiconductors⁴², which estimate the Curie-Weiss transition temperature closed to the experimental findings. The Ginzburg-Landau theory⁴⁶ has been used to describe ferromagnetic properties of Mn-doped semiconductors. A simple model in the low-Mn density regime was proposed⁴⁷, in which holes are allowed to hop to the magnetic impurity sites and interact with the magnetic moments via phenomenological exchange interactions. There are other models based on a polaronic picture where a cloud of Mn-spins are polarized by a single hole⁴⁸. The concept of magnetic percolation picture was introduced to estimate the

observed Curie-Weiss temperature⁴⁹. The ferromagnetic semiconductors have also been studied theoretically using the $\mathbf{k} \cdot \mathbf{p}$ kinetic-exchange effective Hamiltonian^{50,51}. There have been several studies to explain the ferromagnetism in zinc-blende semiconductors using the RKKY exchange interaction^{41,52,54,55}.

An analytical study of RKKY interaction mediated by the states of underlying Luttinger Hamiltonian is still lacking. In this work, we provide an exact analytical expression of the RKKY exchange interaction between two magnetic Mn^{2+} ions in 3D hole-gas (3DHG) that follows the 4×4 Luttinger Hamiltonian. It's form is different from that of 3DEG owing to the multiband nature of the Luttinger system. Our result displays the explicit dependence on the relevant band structure parameters of the Luttinger Hamiltonian. Using the analytical expression of the range function, we determine the contribution of RKKY interaction to the Curie-Weiss temperatures T_C for a ferromagnetic semiconductor ZnMnTe.

The remainder of this paper is organized as follows. In section II, we briefly describe the Kohn-Luttinger Hamiltonian and its basic ground state properties. In section III, we derive an analytical expression of the RKKY interaction in Mn-doped zinc blende semiconductors described by 4×4 Kohn-Luttinger Hamiltonian. In section IV, we compute T_C for ZnMnTe and summarize our results in section V.

II. BASIC INFORMATION

The valence bands of zinc-blende semiconductors can be faithfully described by the 6×6 Kohn-Luttinger Hamiltonian⁵⁶ in the basis of total angular momentum eigenstates $|j, m_j\rangle$: $|3/2, +3/2\rangle$, $|3/2, +1/2\rangle$, $|3/2, -1/2\rangle$, $|3/2, -3/2\rangle$, $|1/2, +1/2\rangle$, $|1/2, -1/2\rangle$ as given by

$$H = \begin{bmatrix} -P - Q & L & -M & 0 & \frac{1}{\sqrt{2}}L & \sqrt{2}M \\ L^\dagger & -P + Q & 0 & M & \sqrt{2}Q & -\sqrt{\frac{3}{2}}L \\ M^\dagger & 0 & -P + Q & -L & -\sqrt{\frac{3}{2}}L^\dagger & -\sqrt{2}Q \\ 0 & M^\dagger & -L^\dagger & -P - Q & -\sqrt{2}M^\dagger & \frac{1}{\sqrt{2}}L^\dagger \\ \frac{1}{\sqrt{2}}L^\dagger & \sqrt{2}Q^\dagger & -\sqrt{\frac{3}{2}}L & -\sqrt{2}M & -P - \Delta_{\text{SO}} & 0 \\ \sqrt{2}M^\dagger & -\sqrt{\frac{3}{2}}L^\dagger & -\sqrt{2}Q^\dagger & \frac{1}{\sqrt{2}}L & 0 & -P - \Delta_{\text{SO}} \end{bmatrix}, \quad (1)$$

where $P = \frac{\gamma_1 \hbar^2 k^2}{2m_0}$, $Q = \frac{\gamma_2 \hbar^2 k^2}{2m_0}(1 - 3 \cos^2 \theta)$, $L = \frac{\sqrt{3} \gamma_3 \hbar^2 k^2}{2m_0} \sin 2\theta e^{-i\phi}$ and $M = \frac{\sqrt{3} \hbar^2 k^2}{2m_0} \sin^2 \theta [\gamma_2 \cos 2\phi - i\gamma_3 \sin 2\phi]$ with (k, θ, ϕ) are the spherical polar coordinates of the wave vector \mathbf{k} . Here m_0 and Δ_{SO} being the bare electron mass and the split-off energy, respectively. The dimensionless Luttinger parameters γ_1 , γ_2 and γ_3 characterize the valence band of the specific semiconductors. The information about the spin-orbit coupling is contained in the parameters γ_2 and γ_3 . Typical band structure of the Kohn-Luttinger Hamiltonian is shown in Fig. 1. We can safely ignore the split-off band if the Fermi energy (E_F) is less than the split-off energy. Hence the upper-left 4×4 matrix block in Eq. (1) describes the two upper most valence bands, usually known as heavy hole and light hole bands, approximately.

Within the spherical approximation⁵⁷, replacing γ_2 and γ_3 by the average value $\gamma_s = 2\gamma_2/5 + 3\gamma_3/5$, the 4×4 Luttinger Hamiltonian² describing heavy-hole and light-hole states is

$$H_0 = \frac{1}{2m_0} \left[\left(\gamma_1 + \frac{5}{2} \gamma_s \right) \mathbf{p}^2 - 2\gamma_s (\mathbf{p} \cdot \mathbf{J})^2 \right]. \quad (2)$$

Here m_0 is the bare electron mass and \mathbf{J} is the spin-3/2

matrix operator. The components of the matrix operator are given by,

$$J_x = \begin{pmatrix} 0 & \frac{\sqrt{3}}{2} & 0 & 0 \\ \frac{\sqrt{3}}{2} & 0 & 1 & 0 \\ 0 & 1 & 0 & \frac{\sqrt{3}}{2} \\ 0 & 0 & \frac{\sqrt{3}}{2} & 0 \end{pmatrix}, \quad (3)$$

$$J_y = i \begin{pmatrix} 0 & -\frac{\sqrt{3}}{2} & 0 & 0 \\ \frac{\sqrt{3}}{2} & 0 & -1 & 0 \\ 0 & 1 & 0 & -\frac{\sqrt{3}}{2} \\ 0 & 0 & \frac{\sqrt{3}}{2} & 0 \end{pmatrix}, \quad (4)$$

$$J_z = \begin{pmatrix} \frac{3}{2} & 0 & 0 & 0 \\ 0 & \frac{1}{2} & 0 & 0 \\ 0 & 0 & -\frac{1}{2} & 0 \\ 0 & 0 & 0 & -\frac{3}{2} \end{pmatrix}. \quad (5)$$

The above Hamiltonian H_0 is rotationally invariant and commutes with the helicity operator $\hat{\Lambda} = \mathbf{k} \cdot \mathbf{J}/k$ so that

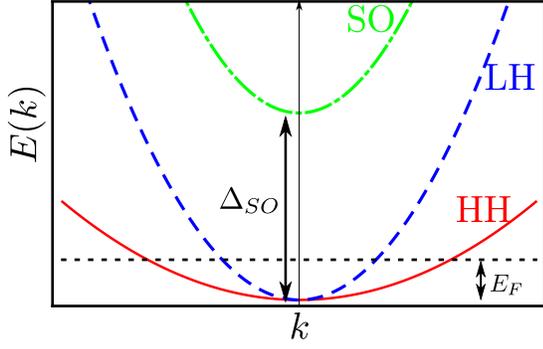


FIG. 1: Sketch of energy dispersion of heavy hole, light hole and split-off bands for p -doped zinc-blende semiconductors.

Compound	a (Å)	γ_1	γ_2	γ_3	γ_s	Δ_{SO} (eV)	E_F (eV)
ZnTe	6.10	3.8	0.72	1.13	1.068	0.96	0.1195
GaAs	5.65	6.98	2.06	2.93	2.58	0.32-0.36	0.1377
GaP	5.45	4.05	0.49	2.93	1.95	0.03-0.13	0.01116

TABLE I: Values of various parameters for the effective Luttinger Hamiltonian of families of zinc-blende semiconductors, from Ref.^{50,51,58}. Typical hole density in these semiconductors varies between $(10^{24} - 10^{26}) \text{ m}^{-3}$. Here, we have taken the hole density $n_h = 1.0 \times 10^{26} \text{ m}^{-3}$ for all of them. It is clear from the table that for this typical order of density, the doubly degenerate two-band Hamiltonian is not applicable for GaAs and GaP, because E_F is of the order of Δ_{SO} . But for ZnTe, $E_F \ll \Delta_{SO}$ ($\Delta_{SO} \approx 8E_F$), so doubly degenerate two-band Luttinger Hamiltonian will be a good approximation. From now onwards we will only focus on ZnTe as an example to elaborate our results.

its eigenvalues $\lambda = \pm 3/2, \pm 1/2$ are good quantum numbers. Here $\lambda = \pm 3/2$ and $\lambda = \pm 1/2$ correspond to the heavy hole and light hole states, respectively. Therefore, the eigenstates of the helicity operator are the same as the eigenstates of the Hamiltonian H_0 . The energy dispersion of the heavy and light hole states are given by $E_{h/l}(\mathbf{k}) = (\hbar k)^2 / (2m_{h/l})$ with $m_{h/l} = m_0 / (\gamma_1 \mp 2\gamma_s)$ are the heavy and light hole masses, respectively. The two-

fold degeneracy of heavy and light hole branches is due to the consequence of the space inversion and time-reversal symmetries of the Luttinger Hamiltonian. Using the basis of eigenstates of J_z , the eigenspinors $|\lambda, \mathbf{k}\rangle$ for $\lambda = 3/2$ and $\lambda = 1/2$ can be written as

$$|3/2, \mathbf{k}\rangle = \begin{pmatrix} \cos^3 \frac{\theta}{2} e^{(-3i/2)\phi} \\ \sqrt{3} \cos^2 \frac{\theta}{2} \sin \frac{\theta}{2} e^{(-i/2)\phi} \\ \sqrt{3} \cos \frac{\theta}{2} \sin^2 \frac{\theta}{2} e^{(i/2)\phi} \\ \sin^3 \frac{\theta}{2} e^{(3i/2)\phi} \end{pmatrix} \quad (6)$$

and

$$|1/2, \mathbf{k}\rangle = \begin{pmatrix} -\sqrt{3} \cos^2 \frac{\theta}{2} \sin \frac{\theta}{2} e^{(-3i/2)\phi} \\ \cos \frac{\theta}{2} \left(\cos^2 \frac{\theta}{2} - 2 \sin^2 \frac{\theta}{2} \right) e^{(-i/2)\phi} \\ \sin \frac{\theta}{2} \left(2 \cos^2 \frac{\theta}{2} - \sin^2 \frac{\theta}{2} \right) e^{(i/2)\phi} \\ \sqrt{3} \cos \frac{\theta}{2} \sin^2 \frac{\theta}{2} e^{(3i/2)\phi} \end{pmatrix}. \quad (7)$$

The remaining spinors for $\lambda = -3/2$ and $\lambda = -1/2$ can easily be obtained from Eq. (6) and Eq. (7) under the spatial inversion operations $\theta \rightarrow \pi - \theta$ and $\phi \rightarrow \pi + \phi$.

Performing the standard procedure, the Fermi energy is given by

$$E_F = \frac{(\hbar k_F^{0e})^2}{2m_0} \left[\frac{\gamma_1^2 - 4\gamma_s^2}{[(\gamma_1 - 2\gamma_s)^{3/2} + (\gamma_1 + 2\gamma_s)^{3/2}]^{2/3}} \right] \quad (8)$$

and the corresponding Fermi wave-vectors $k_F^{h/l}$ for heavy and light-hole bands, respectively, are given by

$$k_F^{h/l} = k_F^{0e} \frac{m_{h/l}^{1/2}}{(m_h^{3/2} + m_l^{3/2})^{1/3}}, \quad (9)$$

where $k_F^{0e} = (3\pi^2 n_h)^{1/3}$ with n_h being the hole density. Also the density of states at Fermi energy is $\rho(E_F) = (m_h^{3/2} + m_l^{3/2})^{2/3} k_F^{0e} / (\pi^2 \hbar^2)$. For a charge carrier with spin s and carrier density n_c , we define $k_F^{0h/0e} = (6\pi^2 n_c / (2s+1))^{1/3}$, where $s = 3/2$ for hole gas and $s = 1/2$ for electron gas, which implies $k_F^{0h} = k_F^{0e} / 2^{1/3}$. Various parameters along with the Fermi energy for three different zinc blende semiconductors are given in Table I.

The Green function $G(\mathbf{k}, \omega + i0^+) = [\omega + i0^+ - H_0]^{-1}$ of the 4×4 Luttinger Hamiltonian is then given by¹⁷

$$G(\mathbf{k}, \omega) = \sum_{\lambda} \frac{1}{E_{\lambda} - \omega - i0^+} \begin{pmatrix} -\frac{1}{2} - \frac{\lambda(1+3\cos(2\theta))}{8} & -\frac{\lambda\sqrt{3}}{4} \sin(2\theta)e^{-i\phi} & -\frac{\lambda\sqrt{3}}{4} \sin^2 \theta e^{-2i\phi} & 0 \\ -\frac{\lambda\sqrt{3}}{4} \sin(2\theta)e^{i\phi} & -\frac{1}{2} + \frac{\lambda(1+3\cos(2\theta))}{8} & 0 & -\frac{\lambda\sqrt{3}}{4} \sin^2 \theta e^{-2i\phi} \\ -\frac{\lambda\sqrt{3}}{4} \sin^2 \theta e^{2i\phi} & 0 & -\frac{1}{2} + \frac{\lambda(1+3\cos(2\theta))}{8} & \frac{\lambda\sqrt{3}}{4} \sin(2\theta)e^{-i\phi} \\ 0 & -\frac{\lambda\sqrt{3}}{4} \sin^2 \theta e^{2i\phi} & \frac{\lambda\sqrt{3}}{4} \sin(2\theta)e^{i\phi} & -\frac{1}{2} - \frac{\lambda(1+3\cos(2\theta))}{8} \end{pmatrix}, \quad (10)$$

which we will use in the next section.

In these semiconductors, the magnetic impurities

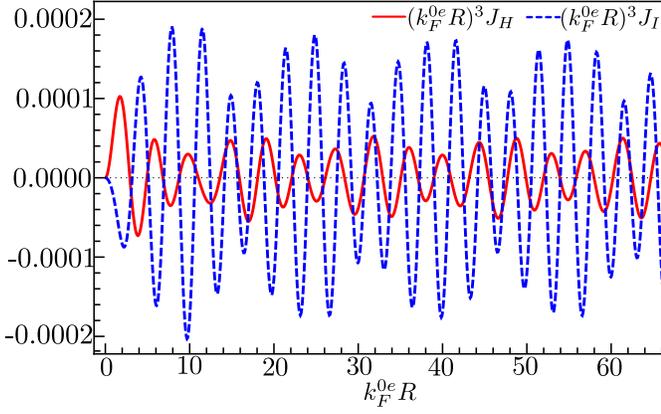


FIG. 2: The range functions of RKKY interaction, from Eqs. 15 and 16, for Mn-doped ZnTe are plotted to show the beating pattern.

(Mn²⁺ state having localised d -orbitals) interact with each other by valance holes (having p -orbital) through the exchange interaction. So we assume p - d type contact exchange interaction between the hole spin $\mathbf{J}(\mathbf{r})$ and the spins of the magnetic impurities \mathbf{S}_j , at positions \mathbf{R}_j as

$$H_{p-d} = J_{pd}^* \sum_{j=1,2} \mathbf{S}_j \cdot \mathbf{J}(\mathbf{r}) \delta(\mathbf{r} - \mathbf{R}_j) \quad (11)$$

with J_{pd}^* is the strength of p - d exchange interaction, whose dimension is energy times volume. Here $J_{pd}^* = J_{pd}/3$, with $J_{pd} = 50 \text{ eV } \text{\AA}^3$ for Mn doped ZnTe dilute magnetic semiconductors⁵¹. Thus the total Hamiltonian of the system is $H = H_0 + H_{p-d}$. By considering H_{p-d} as a perturbation, the RKKY interaction is the second

order correction to the ground state energy of H_0 .

III. RKKY INTERACTION

The RKKY interaction between two impurity spins \mathbf{S}_1 and \mathbf{S}_2 put at a distance \mathbf{R} , at zero temperature, can be computed using second-order perturbation theory and it is expressed as follows

$$H_{\text{RKKY}} = -\frac{J_{pd}^2}{9\pi} \text{Im} \int_{-\infty}^{E_F} d\omega \text{Tr}[(\mathbf{S}_1 \cdot \mathbf{J}) G(\mathbf{R}, \omega + i0^+) \times (\mathbf{S}_2 \cdot \mathbf{J}) G(-\mathbf{R}, \omega + i0^+)], \quad (12)$$

where Tr indicates a trace over the spin degree of freedom. The energy-coordinate representation of the Green's function is given by

$$G(\pm\mathbf{R}, \omega + i0^+) = \int \frac{d^3k}{(2\pi)^3} G(\mathbf{k}, \omega + i0^+) e^{\pm i\mathbf{k} \cdot \mathbf{R}}, \quad (13)$$

where we use the Green's function as in Eq. (10). Without loss of generality, we consider the spins along the z axis (i.e, $\mathbf{R} = R\hat{z}$) and after some tedious algebra, we obtain the RKKY interaction, containing only the Heisenberg and the Ising terms as

$$H_{\text{RKKY}} = J_H \mathbf{S}_1 \cdot \mathbf{S}_2 + J_I S_{1z} S_{2z}, \quad (14)$$

where J_H and J_I denote range functions for the collinear Heisenberg and Ising terms, respectively. The non-collinear Dzyaloshinsky-Moriya (DM)^{59,60} coupling term is absent since the Luttinger Hamiltonian is invariant under spatial inversion. The detail derivation of J_H and J_I are given in the appendix, with the final form being

$$J_H = -\frac{J_{pd}^2}{(2\pi)^3} \left(\frac{m_h}{9\hbar^2 R^4} \right) \left[-\frac{9 \cos(2\zeta_F^h)}{2\zeta_F^h} - \left(\frac{9\delta^2}{2\zeta_F^l} + 2\delta^2 \zeta_F^l \right) \cos(2\zeta_F^l) + \left(-\frac{6\delta^2 \zeta_F^h}{(1+\delta)} + \frac{9(1+\delta)}{2\zeta_F^h} \right) \cos(\zeta_F^h + \zeta_F^l) \right. \\ \left. + \left(-\frac{9}{2} + \frac{9}{4(\zeta_F^h)^2} \right) \sin(2\zeta_F^h) + \left(\frac{5\delta^2}{2} + \frac{9\delta^2}{4(\zeta_F^l)^2} \right) \sin(2\zeta_F^l) - \left(\frac{9}{2(\zeta_F^h)^2} + \frac{(3\delta^3 - 12\delta^2 - 9\delta)}{(1+\delta)^2} \right) \sin(\zeta_F^h + \zeta_F^l) \right. \\ \left. + \frac{9}{2} \text{si}(2\zeta_F^h) - \frac{15\delta^2}{2} \text{si}(2\zeta_F^l) + \left(\frac{15\delta^2}{2} - \frac{9}{2} \right) \text{si}(\zeta_F^h + \zeta_F^l) \right], \quad (15)$$

$$J_I = -\frac{J_{pd}^2}{(2\pi)^3} \left(\frac{3m_h}{18\hbar^2 R^4} \right) \left[\left(\frac{18}{\zeta_F^h} - 3\zeta_F^h \right) \cos(2\zeta_F^h) + \left(\frac{18\delta^2}{\zeta_F^l} + \delta^2 \zeta_F^l \right) \cos(2\zeta_F^l) + \left(\frac{4\delta^2 \zeta_F^h}{1+\delta} - \frac{18(1+\delta)}{\zeta_F^h} \right) \cos(\zeta_F^h + \zeta_F^l) \right. \\ \left. + \left(\frac{27}{2} - \frac{9}{(\zeta_F^h)^2} \right) \sin(2\zeta_F^h) - \left(\frac{\delta^2}{2} + \frac{9\delta^2}{(\zeta_F^l)^2} \right) \sin(2\zeta_F^l) + \left(\frac{18}{(\zeta_F^h)^2} - \frac{4\delta(6+7\delta)}{(1+\delta)^2} \right) \sin(\zeta_F^h + \zeta_F^l) \right. \\ \left. - 6\text{si}(2\zeta_F^h) + 18\delta^2 \text{si}(2\zeta_F^l) + 6(1-3\delta^2) \text{si}(\zeta_F^h + \zeta_F^l) \right], \quad (16)$$

where, $\zeta_F^\lambda = k_F^\lambda R$ and $\delta = \sqrt{m_l/m_h} < 1$ and $\text{si}(x) = \int_0^x \frac{\sin t}{t} dt$ is the sine integral. It is evident from the above

equations that the J_H and J_I oscillate with the distance between the spins, R , with multiple frequencies (due to

the two different Fermi-wave vectors of the spin $s = 3/2$ hole states), giving rise to beating pattern. The variation of J_H and J_I for a typical set of parameters has been

$$J_H \simeq \frac{J_{pd}^2}{(2\pi)^3} \frac{2m_h \delta^2}{9\hbar^2 R^4} \left[\zeta_F^l \cos(2\zeta_F^l) + \frac{3\zeta_F^h}{(1+\delta)} \cos(\zeta_F^h + \zeta_F^l) \right], \quad (17)$$

$$J_I \simeq \frac{J_{pd}^2}{(2\pi)^3} \frac{3m_h}{18\hbar^2 R^4} \left[3\zeta_F^h \cos(2\zeta_F^h) - \delta^2 \zeta_F^l \cos(2\zeta_F^l) + \frac{4\delta^2}{(1+\delta)} \zeta_F^h \cos(\zeta_F^h + \zeta_F^l) \right]. \quad (18)$$

The nature of coupling (ferromagnetic/antiferromagnetic) between the magnetic impurities for a particular semiconductor is determined by the density of holes and the distance between the magnetic impurities.

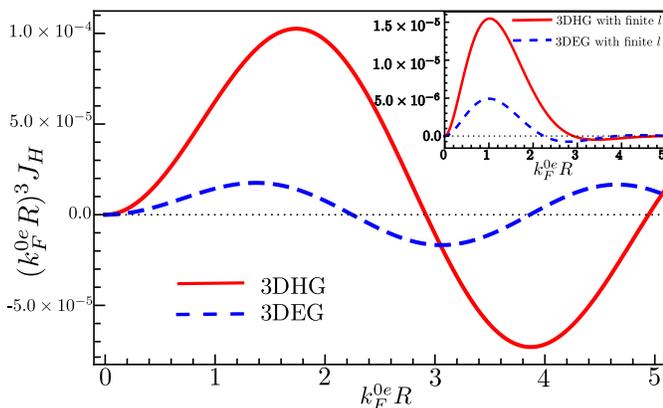


FIG. 3: Comparison of the Heisenberg term of the RKKY interaction for $\text{Zn}_{1-x}\text{Mn}_x\text{Te}$, calculated using 3DEG Hamiltonian with only one band together with different carrier mass ($m_h = 0.5m_0$) and using the Luttinger Hamiltonian for 3DHG with two degenerate bands together with two different masses m_h and m_l . Due to finite mean free path (l) of carriers, the response function decays exponentially. So we have also plotted in the inset of this figure the range function for the Heisenberg term with an exponential decay factor for T_C calculation (see Eq. (21)). Due to this exponential decay, we require only few nearest neighbour distances ($k_F^{0e} R \approx$ upto 2) to compute T_C . We have taken the mean free paths $l = 0.65$ nm and $l = 0.5$ nm for 3DEG case and 3DHG cases respectively.

The RKKY interaction of the hole doped semiconductors is different in nature from that of 3DEG, where such beating pattern is absent due to single band nature. The comparison of the two situations is plotted in Fig. 3. It can be easily checked that the Luttinger Hamiltonian reduces to that of the conventional 3DEG by setting $\gamma_1 = 1$ and $\gamma_s = 0$. In this limit, $m_h = m_l = m_0$ and $k_F^h = k_F^l = k_F^{0h}$, the Ising-like range function exactly vanishes i.e., $J_I = 0$ and the Heisenberg-like range function J_H looks similar to the known form of the conventional

plotted in Fig. 2. For large distances J_H and J_I (upto $1/R^3$ term) can be approximated as

3DEG case^{52,53},

$$J_H = -\frac{2J_{pd}^2 (k_F^{0h})^3}{\pi} \tilde{\chi}_h \mathcal{F}(2k_F^{0h} R), \quad (19)$$

where $\mathcal{F}(y) = \frac{\sin(y) - y \cos(y)}{y^4}$ and $\tilde{\chi}_h = 10m_0 k_F^{0h} / 36\pi^2 \hbar^2$ is the static hole susceptibility. We have written above expression as a function of k_F^{0h} , because in the limiting situation $m_l = m_h$, we will have four degenerate bands.

IV. MEAN-FIELD CURIE-WEISS TEMPERATURE

In this section, we will compute the contribution of the RKKY interaction to the Curie-Weiss temperature. In the mean-field approximation, the Curie-Weiss temperature T_c is given by

$$k_B T_C = \frac{x}{3} S(S+1) J_H^{\text{eff}}, \quad (20)$$

where x is the magnetic dopant concentration, $S = 5/2$ (for magnetic impurity Mn^{+2} state) and spatial average of the Heisenberg-type response J_H^{eff} is given by

$$J_H^{\text{eff}} = \sum_r z_r J_H(r_{ij}) e^{-r_{ij}/l}. \quad (21)$$

Here z_r is the number of r -th neighbors (Ga-Ga), l is carrier transport mean-free path which is introduced as an exponential factor in the effective interaction to take into account the fact that carriers can not pass the information from one magnetic impurity to other magnetic impurities which are situated at distances greater than the mean-free path of the carriers. We have used upto fourth nearest neighbour distances in the above summation, which is sufficient for Mn-doped ZnTe with mean-free path $l = 0.5$ nm.

The origin of ferromagnetism in some dilute magnetic semiconductors is mostly due to the RKKY interaction mediated by valence holes. For these semiconductors, one can calculate T_C , using the given analytical form of J_H with appropriate material parameters like mean free path of itinerant holes and strength of indirect exchange

Mn-fraction	T_C
(x)	(in Kelvin)
0.015	0.48
0.022	0.70
0.043	1.37
0.053	1.69
0.071	2.27

TABLE II: Curie-Weiss temperature T_C of dilute magnetic semiconductor (Zn,Mn)Te for various Mn-fraction x , which is calculated using Eq. (21). Experimental values of T_C : for $\text{Zn}_{1-x}\text{Mn}_x\text{Te}$, $T_C \approx (1 - 10)$ K, for $x = (0.01 - 0.05)$ ^{50,51}.

interaction J_{pd} , provided the density of holes is such that $E_F \ll \Delta_{SO}$. For higher hole densities, two-band approximation will not be valid and one has to take into account the contribution from the split-off band. Then we have to work with 6×6 Kohn-Luttinger Hamiltonian, which will be more complicated. As mentioned in the Table I, for dilute magnetic semiconductors like (Ga,Mn)As, (Ga,Mn)P, our results will not be valid because for these systems hole density is such that Fermi energy becomes comparable with the split-off energy and then there will also be contribution from this band which is not included in our calculation. The critical temperature T_C may also depend on other effects like hole-hole interaction, superexchange etc⁵¹. For just an application of our analytical result, we present in Table II, the calculated T_C of Mn-doped ZnTe dilute magnetic semiconductor for different magnetic dopant concentrations. For this material, we have taken mean free path⁴¹ of the carrier holes $l = 0.5$ nm and the strength of the exchange interaction^{41,50,51} $J_{pd}^* = 50/3 \text{ eV\AA}^3$.

The RKKY interaction through the underlying Luttinger system is markedly different from a 3DEG system, although the resultant T_C computed from either system may match closely. This is because of the small mean free path of the relevant semiconductors. The long range features such as the beating pattern do not have a strong contribution in T_C as the range function is now multiplied by an exponentially decaying function, as shown in Fig. 3. This is the reason for successful prediction of the Curie-Weiss temperature in previous studies based in 3DEG modeling of these systems.

We have also computed the transition temperature T_C using the temperature dependence of the RKKY interaction⁶¹ given by

$$J_H(E_F, R, T) = \int_{-\infty}^{\infty} \frac{J_H(\omega, R)}{4k_B T \cosh^2((E_F - \omega)/2k_B T)} d\omega.$$

For the relevant parameters, $J_H(E_F, R, T)$ depends weakly on the temperature, as shown in Fig. 4, for R

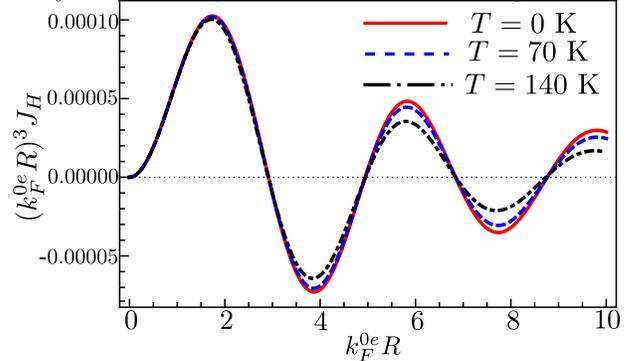


FIG. 4: Temperature dependence of the RKKY interaction strength for Mn-doped ZnTe, showing the change in J_H is small with the temperature for the distance between the impurities contributing to the mean-field T_C calculation.

is of the order of the mean free path. Considering the spatial average $J_H^{\text{eff}}(T)$, defined in equation Eq. (21), one solves Eq. 20 self-consistently to find the transition temperature T_c . As J_H depends weakly on temperature for R is of the order of mean free path, the resulting finite temperature estimation of T_C does not differ significantly from what is presented in Table II.

V. SUMMARY AND CONCLUSIONS

In this work, we have studied RKKY interaction in Mn-doped bulk zinc-blende semiconductors, described by the 4×4 Luttinger Hamiltonian. The analytical form of the interaction, as in Eqs. (15) and (16), describes the effect of the multiple bands through the presence of multiple frequency of oscillation giving rise to beating pattern in the range functions. For systems which are described by 4×4 Luttinger Hamiltonian, we calculate the contribution of the RKKY interaction to the ferromagnetic transition temperature T_C . As an application of our analytical result, we have calculated T_C for a zinc-blende semiconductor (Zn,Mn)Te. We also found that the spin-spin correlation is insensitive to temperature for small distances of the order of mean free path. Therefore finite temperature estimation of T_C does not differ significantly from the estimation at $T = 0$ K.

VI. ACKNOWLEDGEMENT

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Appendix A: Derivation of RKKY interaction

In this section we provide detail derivation of the RKKY interaction. For convenience, we choose $\mathbf{R} = R\hat{z}$ with $R = |\mathbf{R}_1 - \mathbf{R}_2|$. It should be noted here that our results are the same for any arbitrary direction of \mathbf{R} . The Green's function $G(\pm\mathbf{R}, \omega + i0^+)$ is reduced to the following diagonal matrix:

$$G(\pm\mathbf{R}, \omega + i0^+) = \begin{pmatrix} P_0 & 0 & 0 & 0 \\ 0 & Q_0 & 0 & 0 \\ 0 & 0 & Q_0 & 0 \\ 0 & 0 & 0 & P_0 \end{pmatrix}. \quad (\text{A1})$$

Here the diagonal elements P_0 and Q_0 are expressed as $4P_0 = -[I_h^{(1)} + 3I_h^{(2)} + 3I_l^{(1)} - 3I_l^{(2)}]$ and $4Q_0 = -[3I_h^{(1)} - 3I_h^{(2)} + I_l^{(1)} + 3I_l^{(2)}]$ with the integrals $I_\lambda^{(1)}$ and $I_\lambda^{(2)}$ are given by

$$I_\lambda^{(1)} = \int \frac{d^3k}{(2\pi)^3} \frac{e^{ikR \cos \theta}}{(E_\lambda - \omega - i0^+)}, \quad (\text{A2})$$

and

$$I_\lambda^{(2)} = \int \frac{d^3k}{(2\pi)^3} \frac{\cos^2 \theta e^{ikR \cos \theta}}{(E_\lambda - \omega - i0^+)}. \quad (\text{A3})$$

Considering $R > 0$ and performing the three dimensional integrations, we obtain

$$I_\lambda^{(1)} = \frac{m_\lambda}{2\pi\hbar^2} \frac{e^{ik_\lambda R}}{R} \quad (\text{A4})$$

and

$$I_\lambda^{(2)} = \frac{m_\lambda}{\pi\hbar^2 R} \left[\frac{1}{k_\lambda^2 R^2} + e^{ik_\lambda R} \left(\frac{1}{2} + \frac{i}{k_\lambda R} - \frac{1}{k_\lambda^2 R^2} \right) \right] \quad (\text{A5})$$

with $k_\lambda = \sqrt{2m_\lambda(\omega + i0^+)/\hbar^2}$. The above expressions of $I_\lambda^{(1)}$ and $I_\lambda^{(2)}$ remains valid for $R < 0$ as well. Now the final expressions for the components of the Green's function are,

$$P_0 = -\frac{m_h}{2\pi\hbar^2} \frac{e^{ik_h R}}{R} \left(1 + \frac{3i}{2k_h R} - \frac{3}{2k_h^2 R^2} \right) + \frac{3m_l}{4\pi\hbar^2} \frac{e^{ik_l R}}{R} \left(\frac{i}{k_l R} - \frac{1}{k_l^2 R^2} \right) \quad (\text{A6})$$

and

$$Q_0 = \frac{3m_h}{4\pi\hbar^2} \frac{e^{ik_h R}}{R} \left(\frac{i}{k_h R} - \frac{1}{k_h^2 R^2} \right) - \frac{m_l}{2\pi\hbar^2} \frac{e^{ik_l R}}{R} \left(1 + \frac{3i}{2k_h R} - \frac{3}{2k_h^2 R^2} \right). \quad (\text{A7})$$

Using Eq. (A1), Eq. (12) can be reformulated as

$$H_{RKKY} = J_H \mathbf{S}_1 \cdot \mathbf{S}_2 + J_I S_{1z} S_{2z}, \quad (\text{A8})$$

where the integral expressions of J_H and J_I are

$$J_H = -\frac{4J_{pd}^2}{9\pi} \text{Im} \int_{-\infty}^{E_f} Q_0 (3P_0 + 2Q_0) d\omega \quad (\text{A9})$$

$$J_I = -\frac{6J_{pd}^2}{9\pi} \text{Im} \int_{-\infty}^{E_f} (3P_0^2 - Q_0^2 - 2P_0 Q_0) d\omega. \quad (\text{A10})$$

Using Eqs. (A6) and (A7) into the integral expressions of the range functions J_H and J_I and performing the energy integral, the exact analytical expressions of the range functions are

$$\begin{aligned} J_H &= -\frac{J_{pd}^2}{(2\pi)^3} \left(\frac{m_h}{9\hbar^2 R^4} \right) \left[-\frac{9 \cos(2\zeta_F^h)}{2\zeta_F^h} - \left(\frac{9\delta^2}{2\zeta_F^l} + 2\delta^2 \zeta_F^l \right) \cos(2\zeta_F^l) + \left(-\frac{6\delta^2 \zeta_F^h}{(1+\delta)} + \frac{9(1+\delta)}{2\zeta_F^h} \right) \cos(\zeta_F^h + \zeta_F^l) \right. \\ &+ \left(-\frac{9}{2} + \frac{9}{4(\zeta_F^h)^2} \right) \sin(2\zeta_F^h) + \left(\frac{5\delta^2}{2} + \frac{9\delta^2}{4(\zeta_F^l)^2} \right) \sin(2\zeta_F^l) - \left(\frac{9}{2(\zeta_F^h)^2} + \frac{(3\delta^3 - 12\delta^2 - 9\delta)}{(1+\delta)^2} \right) \sin(\zeta_F^h + \zeta_F^l) \\ &\left. + \frac{9}{2} \text{si}(2\zeta_F^h) - \frac{15\delta^2}{2} \text{si}(2\zeta_F^l) + \left(\frac{15\delta^2}{2} - \frac{9}{2} \right) \text{si}(\zeta_F^h + \zeta_F^l) \right], \quad (\text{A11}) \end{aligned}$$

$$\begin{aligned}
J_I = & -\frac{J_{pd}^2}{(2\pi)^3} \left(\frac{3m_h}{18\hbar^2 R^4} \right) \left[\left(\frac{18}{\zeta_F^h} - 3\zeta_F^h \right) \cos(2\zeta_F^h) + \left(\frac{18\delta^2}{\zeta_F^l} + \delta^2 \zeta_F^l \right) \cos(2\zeta_F^l) + \left(\frac{4\delta^2 \zeta_F^h}{1+\delta} - \frac{18(1+\delta)}{\zeta_F^h} \right) \cos(\zeta_F^h + \zeta_F^l) \right. \\
& + \left(\frac{27}{2} - \frac{9}{(\zeta_F^h)^2} \right) \sin(2\zeta_F^h) - \left(\frac{\delta^2}{2} + \frac{9\delta^2}{(\zeta_F^l)^2} \right) \sin(2\zeta_F^l) + \left(\frac{18}{(\zeta_F^h)^2} - \frac{4\delta(6+7\delta)}{(1+\delta)^2} \right) \sin(\zeta_F^h + \zeta_F^l) \\
& \left. - 6\text{si}(2\zeta_F^h) + 18\delta^2 \text{si}(2\zeta_F^l) + 6(1-3\delta^2) \text{si}(\zeta_F^h + \zeta_F^l) \right]. \tag{A12}
\end{aligned}$$

Here, $\text{si}(x) = \int_0^x \frac{\sin t}{t} dt$ is the sine integral.

Appendix B: Derivation of static spin susceptibility

Following Ref.⁵¹, the longitudinal static spin susceptibility for this system can be written as

$$\chi(\mathbf{q}, \mu, T) = \frac{1}{9V} \sum_{\lambda_1, \lambda_2, \mathbf{k}} |\langle \lambda_1, \mathbf{k} | J_z | \lambda_2, \mathbf{k} + \mathbf{q} \rangle|^2 \frac{f(\lambda_1, \mathbf{k}) - f(\lambda_2, \mathbf{k} + \mathbf{q})}{E_{\lambda_2}(\mathbf{k} + \mathbf{q}) - E_{\lambda_1}(\mathbf{k})}, \tag{B1}$$

where $|\lambda, \mathbf{k}\rangle$ is the eigen spinor of the Hamiltonian with eigen energy $E_\lambda(\mathbf{k})$ defined in the main text, $f(\lambda, \mathbf{k}) = 1/(\exp(\beta(E_\lambda(\mathbf{k}) - \mu)) + 1)$ is the Fermi-Dirac distribution function with $\beta = 1/k_B T$ and μ being the chemical potential. We calculate the static spin susceptibility at zero temperature for hole gas by separating out the intraband and interband contributions as $\chi_h(0) = \chi_{\text{intra}}(E_F) + \chi_{\text{inter}}(E_F)$. After some straight forward steps from Eq. (B1), we get

$$\chi_{\text{intra}}(E_F) = \frac{1}{9V} \sum_{\lambda, \mathbf{k}} |\langle \lambda_1, \mathbf{k} | J_z | \lambda_2, \mathbf{k} \rangle|^2 \delta(E_\lambda(\mathbf{k}) - E_F) \tag{B2}$$

and

$$\chi_{\text{inter}}(E_F) = \frac{1}{9V} \sum_{\lambda_1 \neq \lambda_2, \mathbf{k}} |\langle \lambda_1, \mathbf{k} | J_z | \lambda_2, \mathbf{k} \rangle|^2 \frac{\Theta(E_F - E_{\lambda_1}(\mathbf{k})) - \Theta(E_F - E_{\lambda_2}(\mathbf{k}))}{E_{\lambda_2}(\mathbf{k}) - E_{\lambda_1}(\mathbf{k})}. \tag{B3}$$

The intraband and interband matrix elements $\langle \lambda_1, \mathbf{k} | J_z | \lambda_2, \mathbf{k} \rangle$ in terms of polar angle θ of \mathbf{k} are as follows: $\langle \lambda, \mathbf{k} | J_z | \lambda, \mathbf{k} \rangle = \lambda \cos \theta$, $\langle \pm 1/2, \mathbf{k} | J_z | \mp 1/2, \mathbf{k} \rangle = -\sin \theta$, $\langle \pm 3/2, \mathbf{k} | J_z | \pm 1/2, \mathbf{k} \rangle = -(\sqrt{3}/2) \sin \theta$, $\langle \pm 1/2, \mathbf{k} | J_z | \pm 3/2, \mathbf{k} \rangle = -(\sqrt{3}/2) \sin \theta$, $\langle \pm 3/2, \mathbf{k} | J_z | \mp 3/2, \mathbf{k} \rangle = 0$, $\langle \pm 1/2, \mathbf{k} | J_z | \mp 3/2, \mathbf{k} \rangle = 0$, and $\langle \pm 3/2, \mathbf{k} | J_z | \mp 1/2, \mathbf{k} \rangle = 0$.

We calculate the static spin susceptibility using the above matrix elements in Eqs. (B2) and (B3). For intraband contribution to static spin susceptibility $\chi_{\text{intra}}(E_F) = \chi_{\frac{1}{2}}(E_F) + \chi_{\frac{3}{2}}(E_F)$, where contribution from light hole band $\chi_{1/2}(E_F)$ and heavy hole band $\chi_{3/2}(E_F)$ are obtained as $\chi_{\frac{1}{2}}(E_F) = \frac{3m_l k_F^l}{36\pi^2 \hbar^2}$ and $\chi_{\frac{3}{2}}(E_F) = \frac{3m_h k_F^h}{36\pi^2 \hbar^2}$. For interband contribution, $\chi_{\text{inter}}(E_F) = \chi_{\frac{1}{2}, \frac{3}{2}}(E_F) + \chi_{\frac{3}{2}, \frac{1}{2}}(E_F)$, where

$$\chi_{\frac{1}{2}, \frac{3}{2}}(E_F) = \chi_{\frac{3}{2}, \frac{1}{2}}(E_F) = \frac{1}{9\pi^2 \hbar^2} \frac{(k_F^h - k_F^l) m_h m_l}{m_h - m_l}. \tag{B4}$$

Using the expressions of the heavy and light hole Fermi wave vectors $k_F^{h/l}$ given in Eq. (9), the final form of total static spin susceptibility is⁵¹

$$\chi_h(0) = \frac{1}{4} \rho(E_F) \left[\frac{1}{3} + \frac{8}{9} \frac{(m_h^{3/2} m_l - m_l^{3/2} m_h)}{(m_h - m_l)(m_h^{3/2} + m_l^{3/2})} \right]. \tag{B5}$$

Here $\rho(E_F) = (m_h^{3/2} + m_l^{3/2})^{2/3} k_F^{0e} / (\pi^2 \hbar^2)$ is the density of states at the Fermi energy.

Appendix C: Limiting case

The Luttinger Hamiltonian reduces to the Hamiltonian of a 3DHG with four degenerate bands by setting $\gamma_1 = 1$ and $\gamma_s = 0$. In this limit, the static hole spin susceptibility calculated from Eq. (B5) is

$$\tilde{\chi}_h = \frac{10m_0 k_F^{0h}}{36\pi^2 \hbar^2}. \tag{C1}$$

Similarly, setting $\gamma_1 = 1$ and $\gamma_s = 0$ in Eqs. A11 and A12, the Ising-like range function exactly vanishes i.e. $J_I = 0$ and the Heisenberg-like range function J_H becomes

$$J_H = -\frac{2J_{pd}^2(k_F^{0h})^3}{\pi}\tilde{\chi}_h\mathcal{F}(2k_F^{0h}R), \quad (\text{C2})$$

where $\mathcal{F}(y) = \frac{\sin(y)-y\cos(y)}{y^4}$. On the other hand, the analytical form of the RKKY interaction for conventional 3DEG with two degenerate bands is given by⁵²

$$J_H = -\frac{2J_{sd}^2(k_F^{0e})^3}{\pi}\tilde{\chi}_e\mathcal{F}(2k_F^{0e}R), \quad (\text{C3})$$

where $\tilde{\chi}_e = m_0k_F^{0e}/(4\pi^2\hbar^2)$ is the static electron spin susceptibility. So we see from Eqs. (C2) and (C3) that similar relation between RKKY interaction and static spin susceptibility follows for both the cases.

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